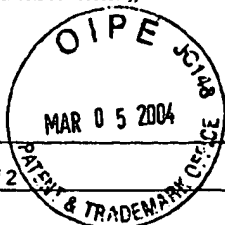


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Application Number	10/602315
Filing Date	June 24, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2812 2829
Examiner Name	Unknown

Attorney Docket No: 1303.107US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
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Asok Kumar Sarkar

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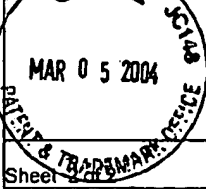
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First Named Inventor	Ahn, Kie
Group Art Unit	2812 2829
Examiner Name	Unknown

Attorney Docket No: 1303.107US1

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